

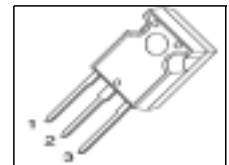
### Cool MOS™ Power Transistor

#### Feature

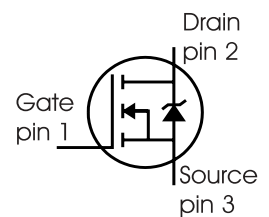
- New revolutionary high voltage technology
- Worldwide best  $R_{DS(on)}$  in TO 247
- Ultra low gate charge
- Periodic avalanche rated
- Extreme  $dv/dt$  rated

$V_{DS}$	800	V
$R_{DS(on)}$	0.29	$\Omega$
$I_D$	17	A

P-TO247



Type	Package	Ordering Code	Marking
SPW17N80C3	P-TO247	Q67040-S4359	17N80C3



#### Maximum Ratings

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25\text{ }^\circ\text{C}$ $T_C = 100\text{ }^\circ\text{C}$	$I_D$	17 11	A
Pulsed drain current, $t_p$ limited by $T_{jmax}$	$I_{D\text{ puls}}$	51	
Avalanche energy, single pulse $I_D = 3.4\text{ A}$ , $V_{DD} = 50\text{ V}$	$E_{AS}$	670	mJ
Avalanche energy, repetitive $t_{AR}$ limited by $T_{jmax}$ <sup>1</sup> $I_D = 17\text{ A}$ , $V_{DD} = 50\text{ V}$	$E_{AR}$	0.5	
Avalanche current, repetitive $t_{AR}$ limited by $T_{jmax}$	$I_{AR}$	17	A
Reverse diode $dv/dt$ $I_S = 17\text{ A}$ , $V_{DS} = 480\text{ V}$ , $T_j = 125\text{ }^\circ\text{C}$	$dv/dt$	6	V/ns
Gate source voltage	$V_{GS}$	$\pm 20$	V
Gate source voltage AC ( $f > 1\text{ Hz}$ )	$V_{GS}$	$\pm 30$	
Power dissipation, $T_C = 25\text{ }^\circ\text{C}$	$P_{tot}$	208	W
Operating and storage temperature	$T_j, T_{stg}$	-55... +150	$^\circ\text{C}$

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Drain Source voltage slope $V_{DS} = 640\text{ V}$ , $I_D = 17\text{ A}$ , $T_j = 125\text{ °C}$	$dv/dt$	50	V/ns

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	$R_{thJC}$	-	-	0.6	K/W
Thermal resistance, junction - ambient, leaded	$R_{thJA}$	-	-	62	
Soldering temperature, 1.6 mm (0.063 in.) from case for 10s	$T_{sold}$	-	-	260	°C

**Electrical Characteristics, at  $T_j=25\text{ °C}$  unless otherwise specified**

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V$ , $I_D=0.25mA$	800	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0V$ , $I_D=17A$	-	870	-	
Gate threshold voltage	$V_{GS(th)}$	$I_D=1000\mu A$ , $V_{GS}=V_{DS}$	2.1	3	3.9	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=800V$ , $V_{GS}=0V$ , $T_j=25\text{ °C}$ , $T_j=150\text{ °C}$	-	0.5	25	$\mu A$
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20V$ , $V_{DS}=0V$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10V$ , $I_D=11A$ , $T_j=25\text{ °C}$ $T_j=150\text{ °C}$	-	0.25	0.29	$\Omega$
Gate input resistance	$R_G$	$f=1MHz$ , open Drain	-	0.7	-	

**Electrical Characteristics** , at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Transconductance	$g_{fs}$	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = 11\text{A}$	-	15	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$	-	2320	-	pF
Output capacitance	$C_{oss}$		-	1250	-	
Reverse transfer capacitance	$C_{rss}$		-	60	-	
Effective output capacitance, <sup>2)</sup> energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 0\text{V to } 480\text{V}$	-	59	-	pF
Effective output capacitance, <sup>3)</sup> time related	$C_{o(tr)}$		-	124	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 400\text{V}$ , $V_{GS} = 0/10\text{V}$ , $I_D = 17\text{A}$ , $R_G = 4.7\Omega$ , $T_j = 125^\circ\text{C}$	-	25	-	ns
Rise time	$t_r$		-	15	-	
Turn-off delay time	$t_{d(off)}$		-	72	82	
Fall time	$t_f$		-	6	9	

**Gate Charge Characteristics**

Gate to source charge	$Q_{gs}$	$V_{DD} = 640\text{V}$ , $I_D = 17\text{A}$	-	12	-	nC
Gate to drain charge	$Q_{gd}$		-	46	-	
Gate charge total	$Q_g$	$V_{DD} = 640\text{V}$ , $I_D = 17\text{A}$ , $V_{GS} = 0\text{ to } 10\text{V}$	-	91	177	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 640\text{V}$ , $I_D = 17\text{A}$	-	6	-	V

<sup>1</sup> Repetitive avalanche causes additional power losses that can be calculated as  $P_{AV} = E_{AR} \cdot f$ .

<sup>2</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

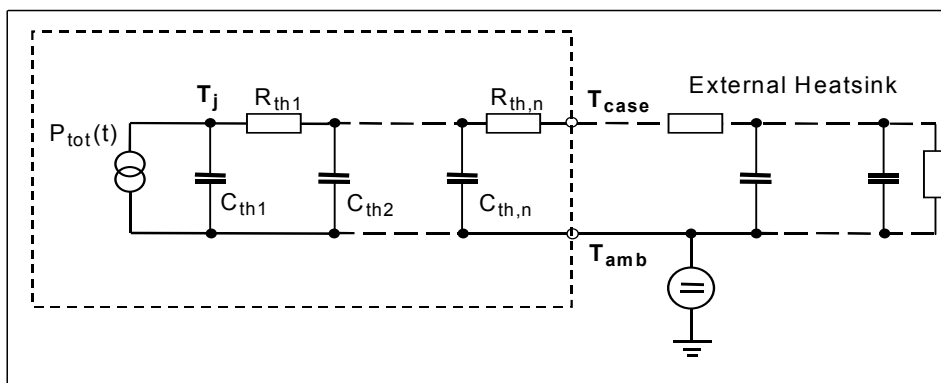
<sup>3</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

**Electrical Characteristics**, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	$I_S$	$T_C=25^\circ\text{C}$	-	-	17	A
Inverse diode direct current, pulsed	$I_{SM}$		-	-	51	
Inverse diode forward voltage	$V_{SD}$	$V_{GS}=0\text{V}, I_F=I_S$	-	1	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=400\text{V}, I_F=I_S,$	-	550	-	ns
Reverse recovery charge	$Q_{rr}$	$di_F/dt=100\text{A}/\mu\text{s}$	-	15	-	$\mu\text{C}$
Peak reverse recovery current	$I_{rrm}$		-	51	-	A
Peak rate of fall of reverse recovery current	$di_{rr}/dt$		-	1200	-	$\text{A}/\mu\text{s}$

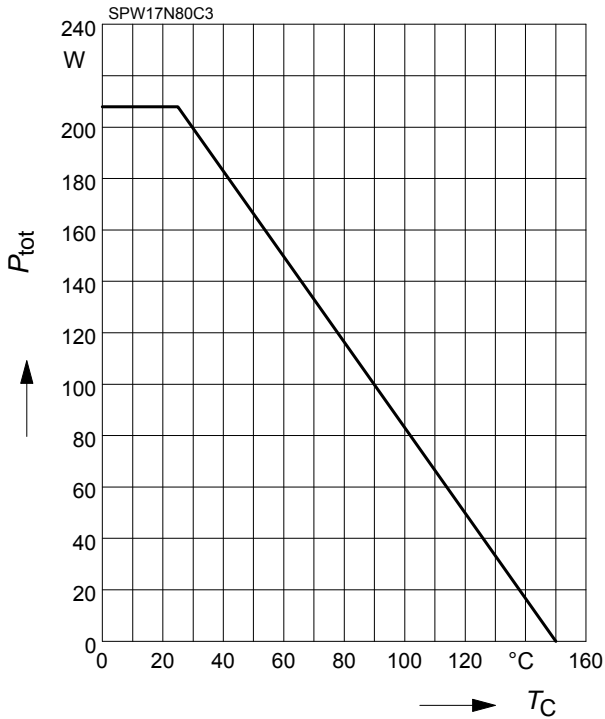
**Typical Transient Thermal Characteristics**

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
$R_{th1}$	0.00812	K/W	$C_{th1}$	0.0003562	Ws/K
$R_{th2}$	0.016		$C_{th2}$	0.001337	
$R_{th3}$	0.031		$C_{th3}$	0.001831	
$R_{th4}$	0.114		$C_{th4}$	0.005033	
$R_{th5}$	0.135		$C_{th5}$	0.012	
$R_{th6}$	0.059		$C_{th6}$	0.092	



**1 Power dissipation**

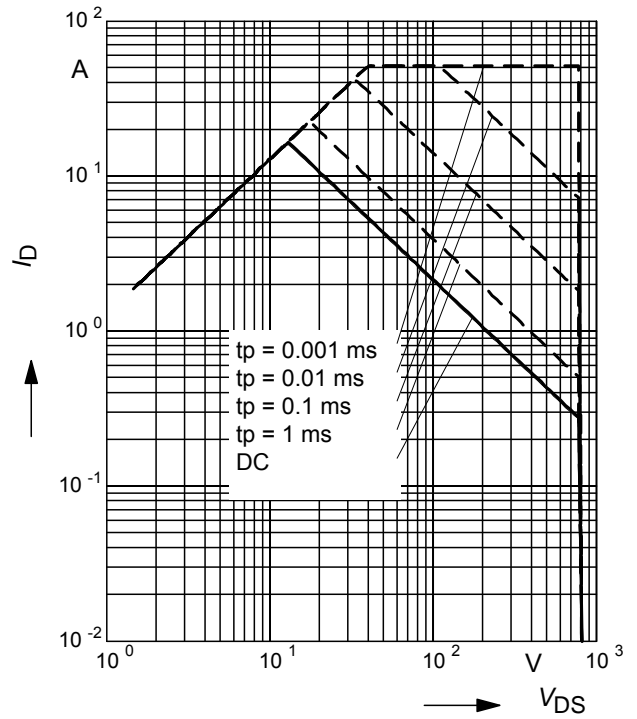
$$P_{tot} = f(T_C)$$



**2 Safe operating area**

$$I_D = f(V_{DS})$$

parameter :  $D = 0$  ,  $T_C = 25^\circ\text{C}$



**3 Safe operating area FullPAK**

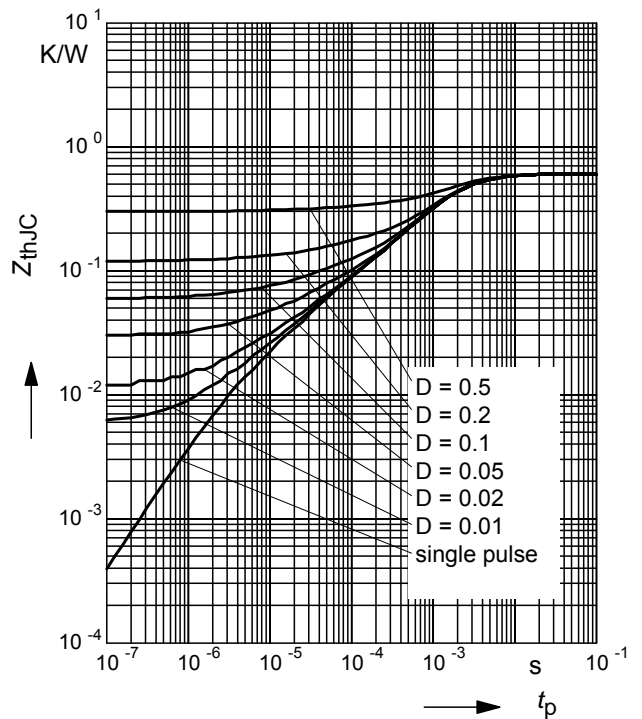
$$I_D = f(V_{DS})$$

parameter:  $D = 0$  ,  $T_C = 25^\circ\text{C}$

**4 Transient thermal impedance**

$$Z_{thJC} = f(t_p)$$

parameter:  $D = t_p/T$



**5 Transient thermal impedance FullPAK**

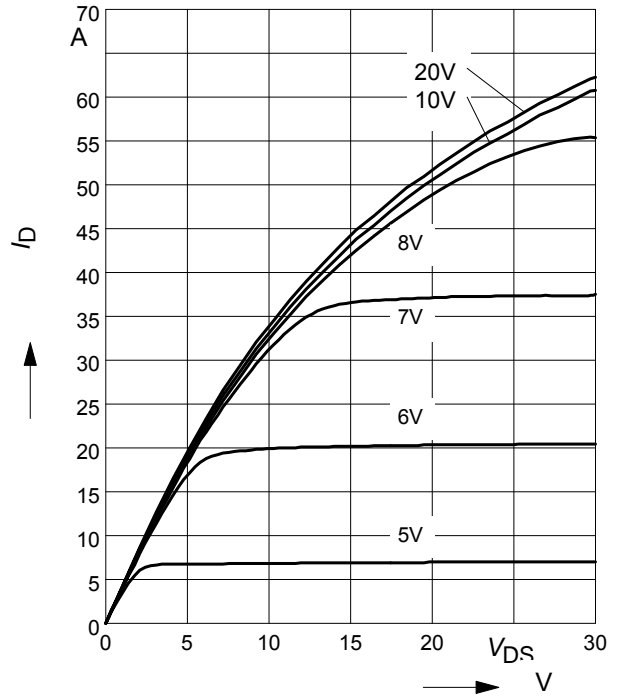
$$Z_{thJC} = f(t_p)$$

parameter:  $D = t_p/t$

**6 Typ. output characteristic**

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

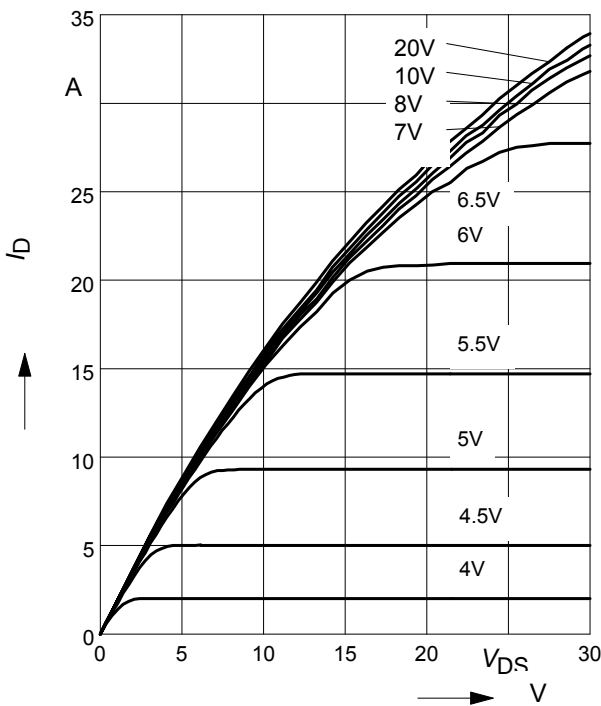
parameter:  $t_p = 10 \mu\text{s}, V_{GS}$



**7 Typ. output characteristic**

$$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$$

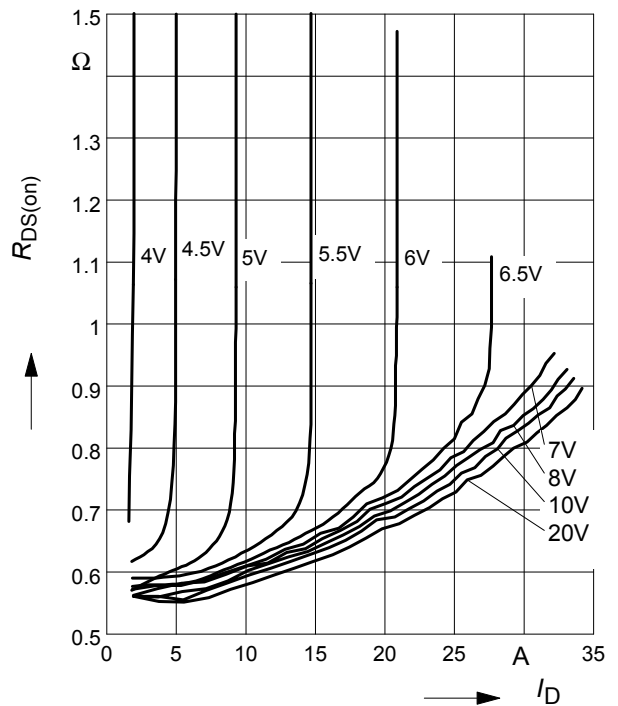
parameter:  $t_p = 10 \mu\text{s}, V_{GS}$



**8 Typ. drain-source on resistance**

$$R_{DS(on)} = f(I_D)$$

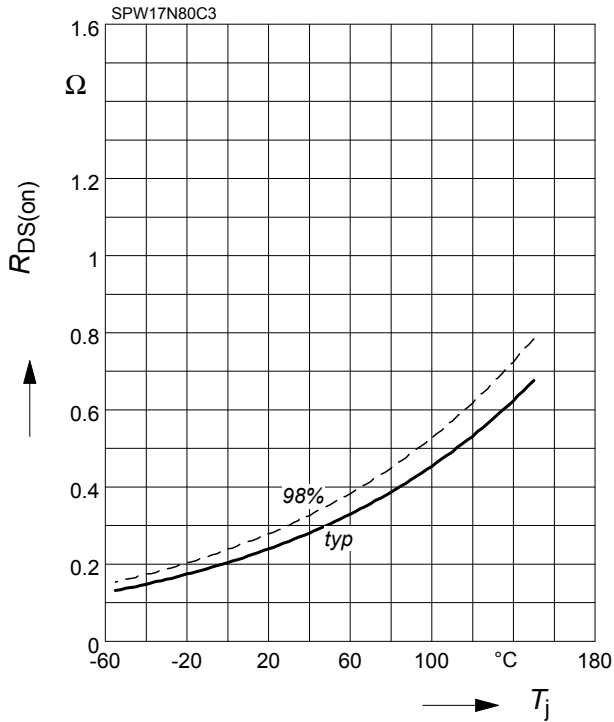
parameter:  $T_j = 150^\circ\text{C}, V_{GS}$



**9 Drain-source on-state resistance**

$$R_{DS(on)} = f(T_j)$$

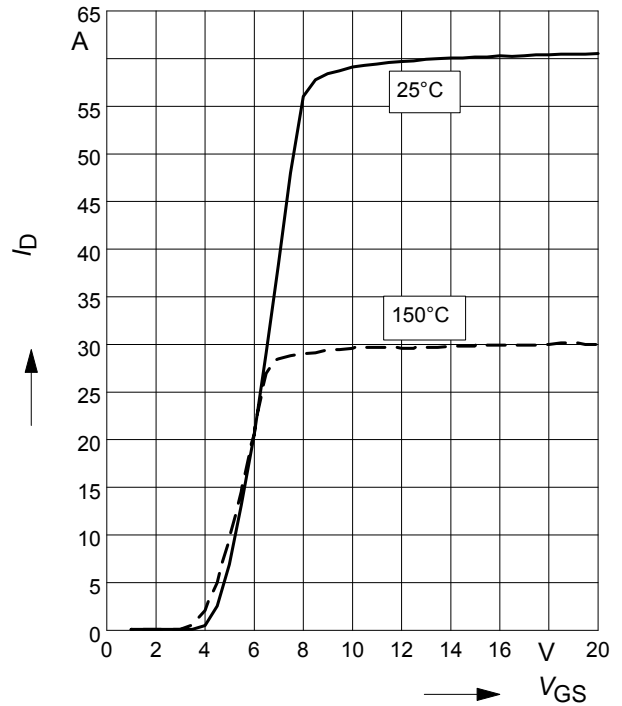
parameter:  $I_D = 11 \text{ A}$ ,  $V_{GS} = 10 \text{ V}$



**10 Typ. transfer characteristics**

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

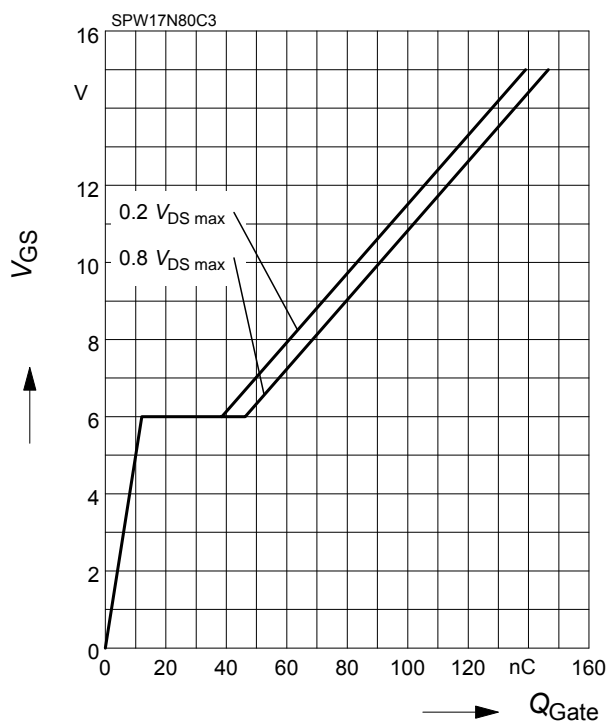
parameter:  $t_p = 10 \mu\text{s}$



**11 Typ. gate charge**

$$V_{GS} = f(Q_{Gate})$$

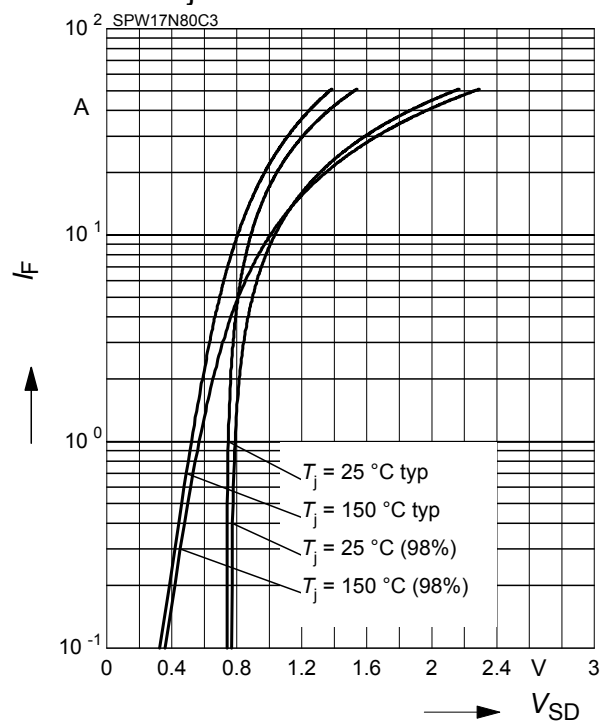
parameter:  $I_D = 17 \text{ A}$  pulsed



**12 Forward characteristics of body diode**

$$I_F = f(V_{SD})$$

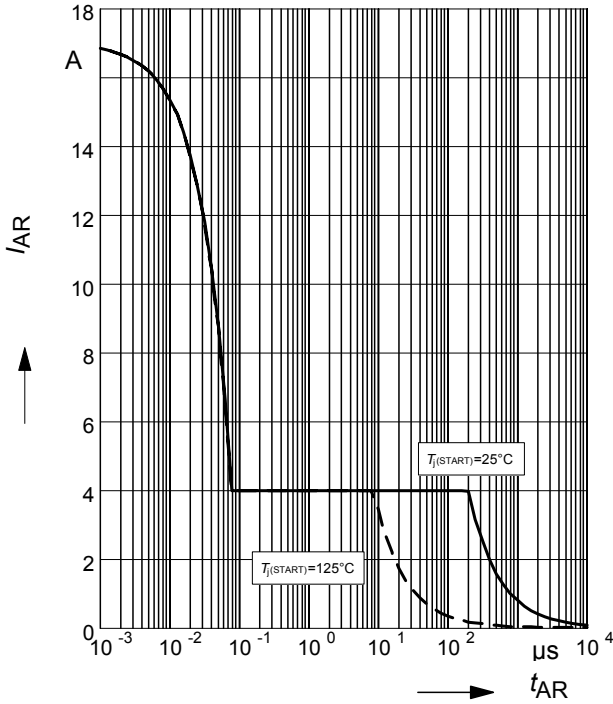
parameter:  $T_j$ ,  $t_p = 10 \mu\text{s}$



**13 Avalanche SOA**

$I_{AR} = f(t_{AR})$

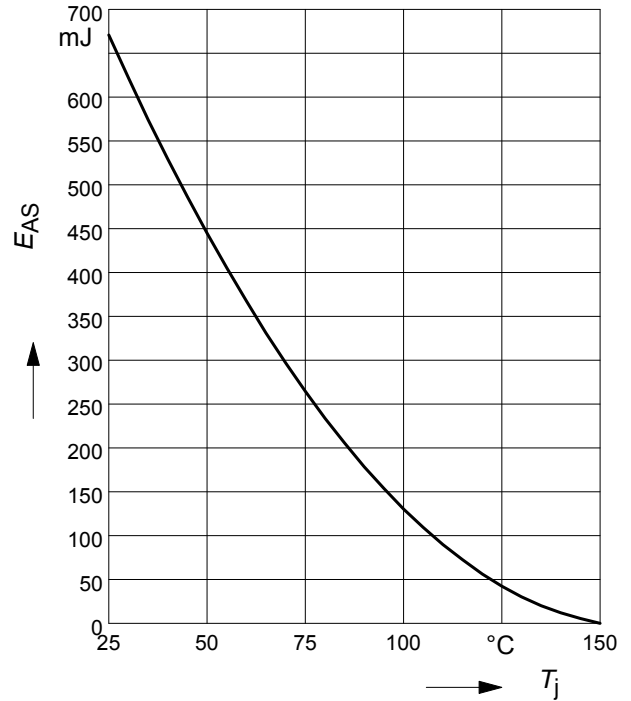
par.:  $T_j \leq 150\text{ }^\circ\text{C}$



**14 Avalanche energy**

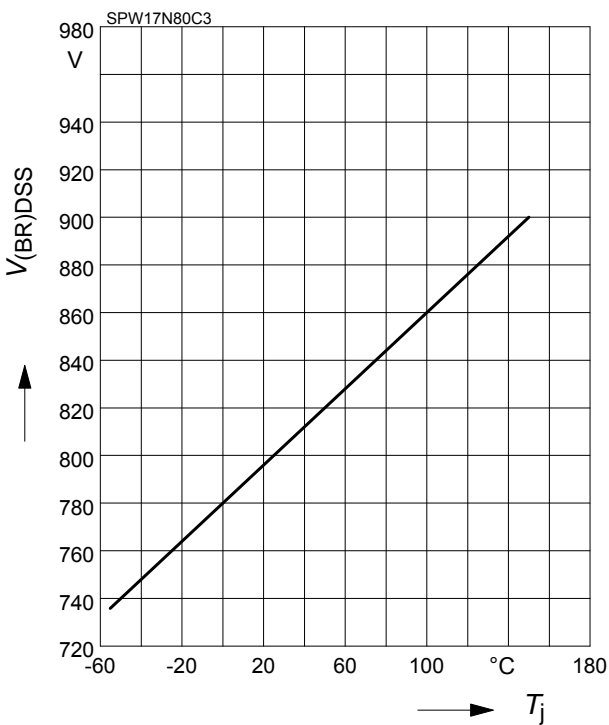
$E_{AS} = f(T_j)$

par.:  $I_D = 3.4\text{ A}$ ,  $V_{DD} = 50\text{ V}$



**15 Drain-source breakdown voltage**

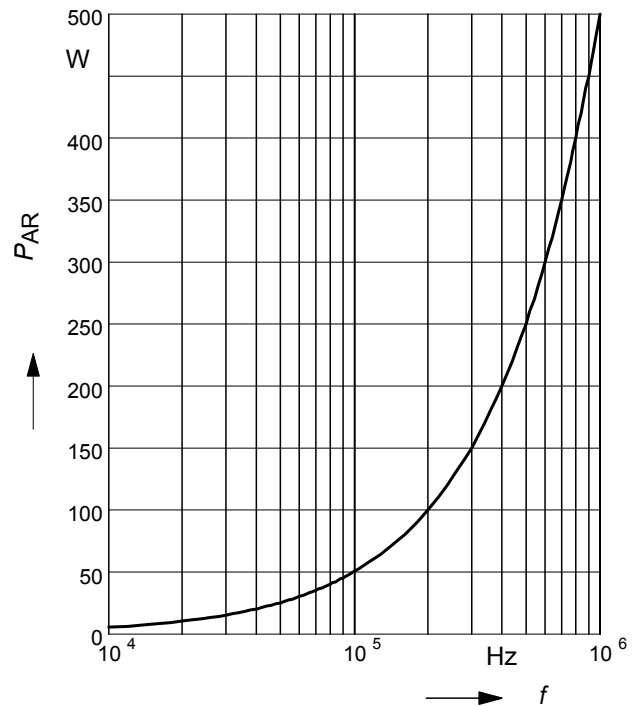
$V_{(BR)DSS} = f(T_j)$



**16 Avalanche power losses**

$P_{AR} = f(f)$

parameter:  $E_{AR} = 0.5\text{ mJ}$

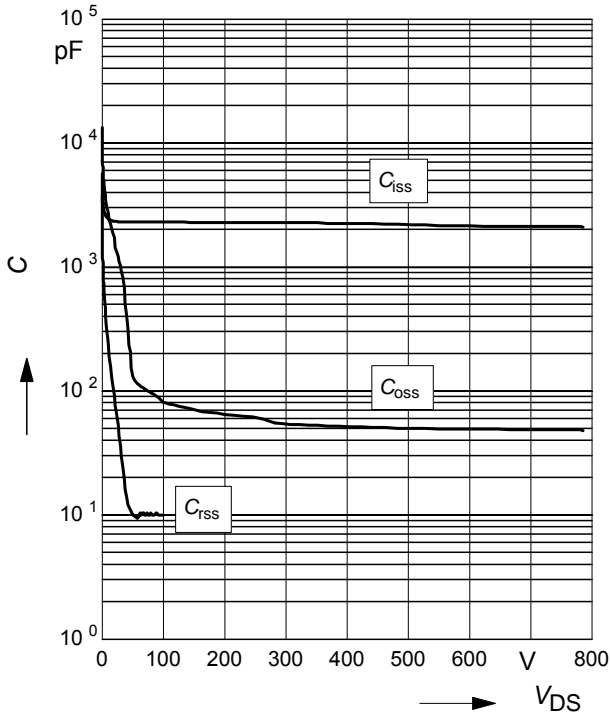




**17 Typ. capacitances**

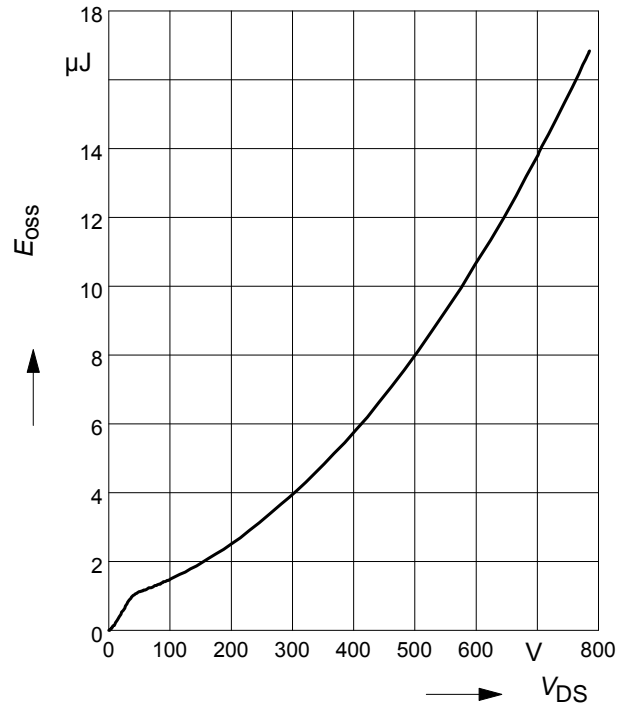
$C = f(V_{DS})$

parameter:  $V_{GS}=0V, f=1\text{ MHz}$

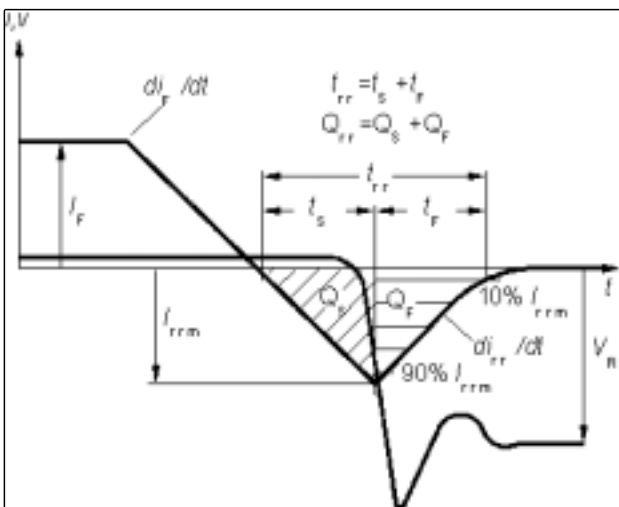


**18 Typ. C<sub>oss</sub> stored energy**

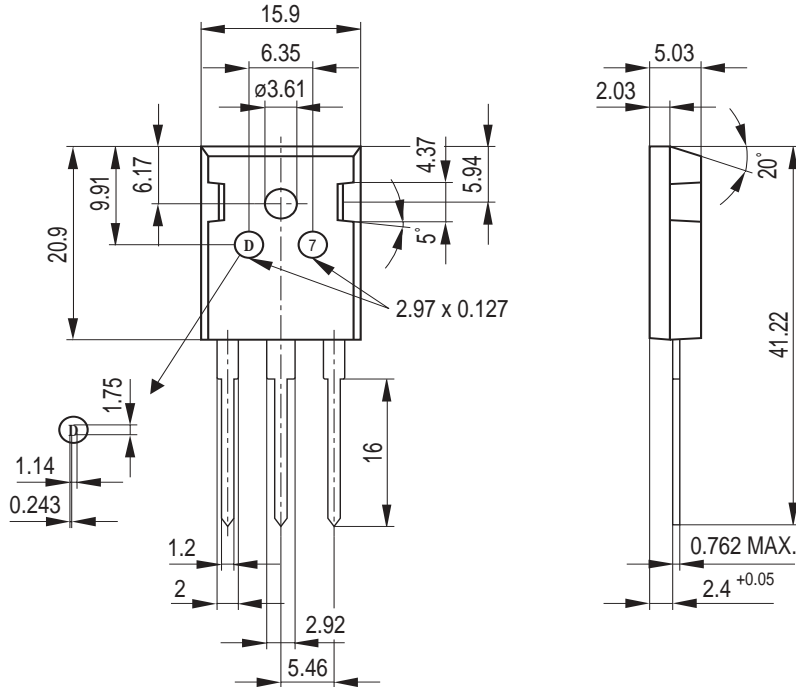
$E_{Oss} = f(V_{DS})$



**Definition of diodes switching characteristics**



P-TO-247-3-1



General tolerance unless otherwise specified: Leadframe parts:  $\pm 0.05$   
 Package parts:  $\pm 0.12$

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